

ABSTRACT OF THE DISCLOSURE

A semiconductor device for use in includes a base and emitter shorted by means of a surface electrode. The surface electrode of a vertical-type bipolar transistor in which a
5 P-type epitaxial growth layer and a P-type semiconductor substrate form the collector is electrically connected to the drain electrode of a lateral MOSFET by means of a metal electrode wiring. Upon application of a high ESD voltage and high surge voltage, the energy of the ESD and surge is absorbed
10 by operation of the vertical-type bipolar transistor and is limited to a voltage equal to or less than the breakdown voltage of the lateral MOSFET that was to be destroyed.